

## 3-PHASE BRIDGE DRIVER

### Features

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage
- dv/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for all channels
- Over-current shutdown turns off all six drivers
- Independent half-bridge drivers
- Matched propagation delay for all channels
- Outputs out of phase with inputs

### Description

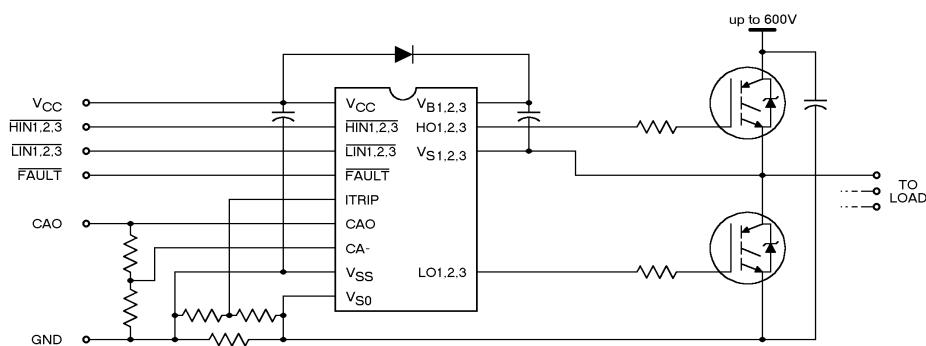
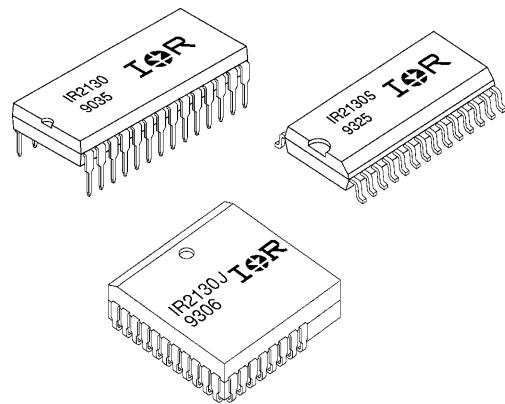
The IR2130 is a high voltage, high speed power MOSFET and IGBT driver with three independent high and low side referenced output channels. Proprietary HVIC technology enables ruggedized monolithic construction. Logic inputs are compatible with 5V CMOS or LSTTL outputs. A ground-referenced operational amplifier provides analog feedback of bridge current via an external current sense resistor. A current trip function which terminates all six outputs is also derived from this resistor. An open drain FAULT signal indicates if an over-current or undervoltage shutdown has occurred. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use at high frequencies. The floating channels can be used to drive N-channel power MOSFETs or IGBTs in the high side configuration which operate up to 600 volts.

### Typical Connection

### Product Summary

<b>V<sub>OFFSET</sub></b>	<b>600V max.</b>
<b>I<sub>O</sub>+/-</b>	<b>200 mA / 420 mA</b>
<b>V<sub>OUT</sub></b>	<b>10 - 20V</b>
<b>t<sub>on/off</sub> (typ.)</b>	<b>675 &amp; 425 ns</b>
<b>Deadtime (typ.)</b>	<b>2.5 <math>\mu</math>s</b>

### Packages



**bsoiuue Maximum Rbtongs**

Absxlmtn Matimus iadicgt nuitiae s stainsdblymtn heco dawaiehtdamhge eoiteemdyvocc ma lc ur.tAll valrageepara - rrebs aeuasollate oetages rdfr nSe. To V<sub>S0</sub>. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions. Additional information s sFognrin 5iguheo g0 t3riu,hP5r.

eyibil	ra,aaeuer DnMnntioa	Value	
	MiU.	Msx,	Bn,t,
V <sub>i1h2S3</sub>	H gl aiiiegFloptin outpm,Vol3a5e	-0.S	52,
V <sub>i1,2S3</sub>	H gl aidegFOoften Oftset,VBl,a,e	V <sub>152V31-23</sub>	+B0,3,+ 1.3
V <sub>HOg, ,i</sub>	eiFhoStde loaptgVOutaueV0t2g3	-S1,3,V 1 2.3	+B0,3,i + C.3
V <sub>Cd</sub>	on ioeia diLegicuFixydVSIpale -o.t,g5	-0S3	2o
V <sub>S</sub>	LugdcVGro-n2	,CC 25	V <sub>IC</sub> + 0.3
V <sub>LO1,2,3</sub>	Low Side Output Voltage	-0.3	V <sub>CC</sub> + 0.3
V <sub>IN</sub>	Logic Input Voltage (HIN1,2,3, LIN1,2,3 & ITRIP)	V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3
V <sub>FLT</sub>	FAULT Output Voltage	3sv C+0	3C <sub>1</sub> V A.3
V <sub>CAO</sub>	Oae amilnfl A plipitrVOutauu ,oSt ge	V <sub>SC</sub> -0.3	V <sub>IC</sub> V+A0.3
V <sub>CA-</sub>	OaeramilnfileA pnrietrln vrnui golputpVViSa-e	3sv C+.3	3C <sub>1</sub> V /t
dlswdb	AlOowael uffsytl Spale Voatsge tr—n5i,n/	s	50
P <sub>e</sub>	PawkrD soier iins@pTt on 2 TA, $\leq$ 2+ 5eC (28PLea, .lI)	—	1.5
	(28PLea—106C)	,	1.(
	(44 Ce,d,P.CI)	—	2.0
R <sub>θaA</sub>	TeeimtlnRes suanci, Jtn tmon no Ambient (28 Lead DIP)	—	83
	(28 Lead SOIC)	—	78
	(44 Lead PLCC)	—	63
T <sub>J</sub>	Junction Temperature	—	150
T <sub>S</sub>	Storage Temperature	-55	150
T <sub>L</sub>	Lead ueep(rotdre nS,l1e iego d0)s—con0s)	,	,0`

**Recommended Operating Conditions**

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to V<sub>S0</sub>. The V<sub>S</sub> offset rating is tested with all supplies biased at 15V differential. Typical ratings at other bias conditions are shown in Figure 54.

Symbol	Parameter Definition	Value		Units
		Min.	Max.	
V <sub>B1,2,3</sub>	High Side Floating Supply Voltage	V <sub>S1,2,3</sub> + 10	V <sub>S1,2,3</sub> + 20	V
V <sub>S1,2,3</sub>	High Side Floating Offset Voltage	Note 1	600	
V <sub>HO1,2,3</sub>	High Side Floating Output Voltage	V <sub>S1,2,3</sub>	V <sub>B1,2,3</sub>	
V <sub>CC</sub>	Low Side and Logic Fixed Supply Voltage	10	20	
V <sub>SS</sub>	Logic Ground	-5	5	
V <sub>LO1,2,3</sub>	Low Side Output Voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic Input Voltage (HIN1,2,3, LIN1,2,3 & ITRIP)	V <sub>SS</sub>	V <sub>SS</sub> + 5	
V <sub>FLT</sub>	FAULT Output Voltage	V <sub>SS</sub>	V <sub>CC</sub>	
V <sub>CAO</sub>	Operational Amplifier Output Voltage	V <sub>SS</sub>	5	
V <sub>CA-</sub>	Operational Amplifier Inverting Input Voltage	V <sub>SS</sub>	5	
T <sub>A</sub>	Ambient Temperature	-40	125	°C

Note 1: Logic operational for V<sub>S</sub> of (V<sub>S0</sub> - 5V) to (V<sub>S0</sub> + 600V). Logic state held for V<sub>S</sub> of (V<sub>S0</sub> - 5V) to (V<sub>S0</sub> - V<sub>BS</sub>).

## Dynamic Electrical Characteristics

V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS1,2,3</sub>) = 15V, V<sub>S0,1,2,3</sub> = V<sub>SS</sub>, C<sub>L</sub> = 1000 pF and T<sub>A</sub> = 25°C unless otherwise specified. The dynamic electrical characteristics are defined in Figures 3 through 5.

Symbol	Parameter Definition	Figure	Value			Units	Test Conditions
			Min.	Typ.	Max.		
t <sub>on</sub>	Turn-On Propagation Delay	11	500	675	850	ns	V <sub>IN</sub> = 0 & 5V V <sub>S1,2,3</sub> = 0 to 600V
t <sub>off</sub>	Turn-Off Propagation Delay	12	300	425	550		
t <sub>r</sub>	Turn-On Rise Time	13	—	80	125		
t <sub>f</sub>	Turn-Off Fall Time	14	—	35	55		
t <sub>itrip</sub>	ITRIP to Output Shutdown Prop. Delay	15	400	660	920	μs	V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V V <sub>ITRIP</sub> = 1V
t <sub>bl</sub>	ITRIP Blanking Time	—	—	400	—		V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V
t <sub>flt</sub>	ITRIP to FAULT Indication Delay	16	335	590	845		V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V
t <sub>flt,in</sub>	Input Filter Time (All Six Inputs)	—	—	310	—		V <sub>IN</sub> = 0 & 5V
t <sub>fltcclr</sub>	LIN1,2,3 to FAULT Clear Time	17	6.0	9.0	12.0	V/μs	V <sub>IN</sub> , V <sub>ITRIP</sub> = 0 & 5V
DT	Deadtime	18	1.3	2.5	3.7		V <sub>IN</sub> = 0 & 5V
SR+	Operational Amplifier Slew Rate (+)	19	4.4	6.2	—	V/μs	
SR-	Operational Amplifier Slew Rate (-)	20	2.4	3.2	—		

## Static Electrical Characteristics

V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS1,2,3</sub>) = 15V, V<sub>S0,1,2,3</sub> = V<sub>SS</sub> and T<sub>A</sub> = 25°C unless otherwise specified. The V<sub>IN</sub>, V<sub>TH</sub> and I<sub>IN</sub> parameters are referenced to V<sub>SS</sub> and are applicable to all six logic input leads: HIN1,2,3 & LIN1,2,3. The V<sub>O</sub> and I<sub>O</sub> parameters are referenced to V<sub>S0,1,2,3</sub> and are applicable to the respective output leads: HO1,2,3 or LO1,2,3.

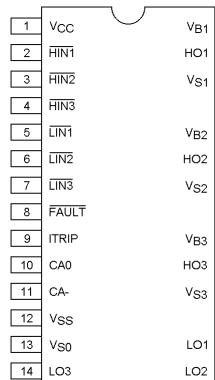
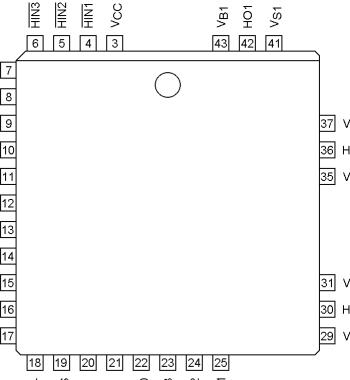
Symbol	Parameter Definition	Figure	Value			Units	Test Conditions
			Min.	Typ.	Max.		
V <sub>IH</sub>	Logic "0" Input Voltage (OUT = LO)	21	2.2	—	—	mV	
V <sub>IL</sub>	Logic "1" Input Voltage (OUT = HI)	22	—	—	0.8		V <sub>IN</sub> = 0V, I <sub>O</sub> = 0A
V <sub>IT,TH+</sub>	ITRIP Input Positive Going Threshold	23	400	490	580		V <sub>IN</sub> = 5V, I <sub>O</sub> = 0A
V <sub>OH</sub>	High Level Output Voltage, V <sub>BIAS</sub> - V <sub>O</sub>	24	—	—	100		V <sub>B</sub> = V <sub>S</sub> = 600V
V <sub>OL</sub>	Low Level Output Voltage, V <sub>O</sub>	25	—	—	100		V <sub>IN</sub> = 0V or 5V
I <sub>LK</sub>	Offset Supply Leakage Current	26	—	—	50		I <sub>TRIP</sub> = 5V
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	27	—	15	30		I <sub>TRIP</sub> = 0V
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> Supply Current	28	—	3.0	4.0		V <sub>IN</sub> = 0V or 5V
I <sub>IN+</sub>	Logic "1" Input Bias Current (OUT = HI)	29	—	450	650	μA	
I <sub>IN-</sub>	Logic "0" Input Bias Current (OUT = LO)	30	—	225	400		V <sub>IN</sub> = 5V
I <sub>ITRIP+</sub>	"High" ITRIP Bias Current	31	—	75	150		
I <sub>ITRIP-</sub>	"Low" ITRIP Bias Current	32	—	—	100		
V <sub>BSUV+</sub>	V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	33	7.5	8.35	9.2	nA	
V <sub>BSUV-</sub>	V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	34	7.1	7.95	8.8		
V <sub>CCUV+</sub>	V <sub>CC</sub> Supply Undervoltage Positive Going Threshold	35	8.3	9.0	9.7		
V <sub>CCUV-</sub>	V <sub>CC</sub> Supply Undervoltage Negative Going Threshold	36	8.0	8.7	9.4		
R <sub>on,FLT</sub>	FAULT Low On-Resistance	37	—	55	75	Ω	

**Static Electrical Characteristics -- Continued**

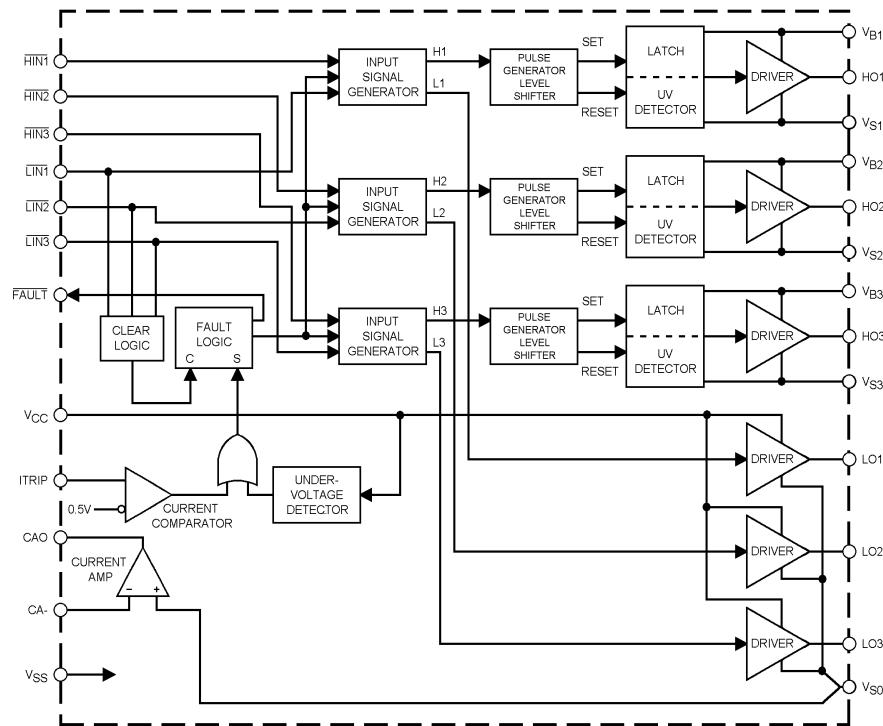
$V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS1,2,3}$ ) = 15V,  $V_{S0,1,2,3}$  =  $V_{SS}$  and  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ ,  $V_{TH}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}$  and are applicable to all six logic input leads:  $HIN1,2,3$  &  $LIN1,2,3$ . The  $V_O$  and  $I_O$  parameters are referenced to  $V_{S0,1,2,3}$  and are applicable to the respective output leads:  $HO1,2,3$  or  $LO1,2,3$ .

Symbol	Parameter Definition	Figure	Value Min.	Value Typ.	Value Max.	Units	Test Conditions
$I_{O+}$	Output High Short Circuit Pulsed Current	38	200	250	—	mA	$V_O = 0V, V_{IN} = 0V$ $PW \leq 10 \mu s$
$I_{O-}$	Output Low Short Circuit Pulsed Current	39	420	500	—		$V_O = 15V, V_{IN} = 5V$ $PW \leq 10 \mu s$
$V_{OS}$	Operational Amplifier Input Offset Voltage	40	—	—	30	mV	$V_{S0} = V_{CA-} = 0.2V$
$I_{CA-}$	CA- Input Bias Current	41	—	—	4.0	nA	$V_{CA-} = 2.5V$
$CMRR$	Op. Amp. Common Mode Rejection Ratio	42	60	80	—	dB	$V_{S0}=V_{CA-}=0.1V$ & 5V
$PSRR$	Op. Amp. Power Supply Rejection Ratio	43	55	75	—		$V_{S0}=V_{CA-}=0.2V$ $V_{CC} = 10V$ & 20V
$V_{OH,AMP}$	Op. Amp. High Level Output Voltage	44	5.0	5.2	5.4	V	$V_{CA-} = 0V, V_{S0} = 1V$
$V_{OL,AMP}$	Op. Amp. Low Level Output Voltage	45	—	—	20	mV	$V_{CA-} = 1V, V_{S0} = 0V$
$I_{SRC,AMP}$	Op. Amp. Output Source Current	46	2.3	4.0	—	mA	$V_{CA-} = 0V, V_{S0} = 1V$ $V_{CAO} = 4V$
$I_{SRC,AMP}$	Op. Amp. Output Sink Current	47	1.0	2.1	—		$V_{CA-} = 1V, V_{S0} = 0V$ $V_{CAO} = 2V$
$I_{O+,AMP}$	Operational Amplifier Output High Short Circuit Current	48	—	4.5	6.5		$V_{CA-} = 0V, V_{S0} = 5V$ $V_{CAO} = 0V$
$I_{O-,AMP}$	Operational Amplifier Output Low Short Circuit Current	49	—	3.2	5.2		$V_{CA-} = 5V, V_{S0} = 0V$ $V_{CAO} = 5V$

**Lead Assignments**

		
28 Lead DIP	44 Lead PLCC w/o 12 Leads	28 Lead SOIC (Wide Body)
<b>IR2130</b>	<b>IR2130J</b>	<b>IR2130S</b>
<b>Part Number</b>		

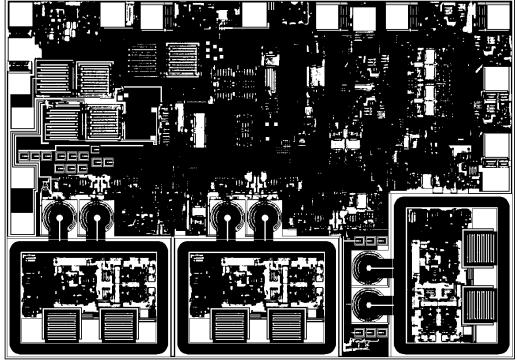
## Functional Block Diagram

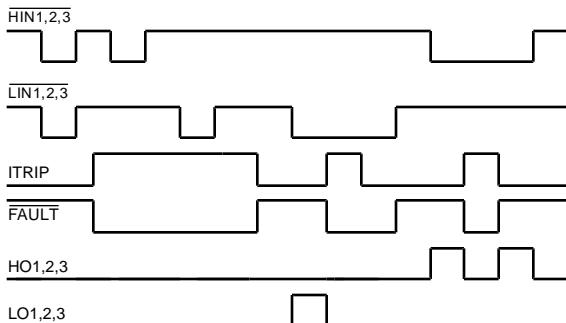


## Lead Definitions

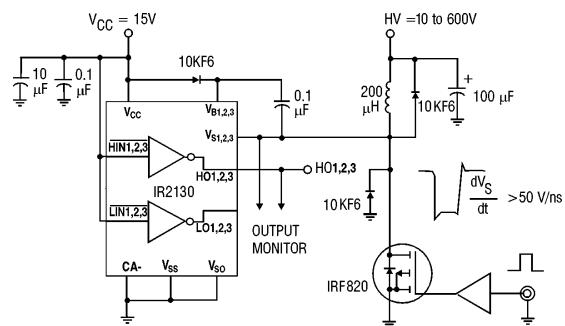
Lead Symbol	Description
HIN1,2,3	Logic inputs for high side gate driver outputs (HO1,2,3), out of phase
LIN1,2,3	Logic inputs for low side gate output (LO1,2,3), out of phase
FAULT	Indicates over-current or undervoltage lockout (low side) has occurred, negative logic
VCC	Low side and logic fixed supply
ITRIP	Input for over-current shutdown
CAO	Output of current amplifier
CA-	Negative input of current amplifier
VSS	Logic ground
VB1,2,3	High side floating supplies
HO1,2,3	High side gate drive outputs
VS1,2,3	High side floating supply returns
LO1,2,3	Low side gate drive outputs
VS0	Low side return and positive input of current amplifier

## Device Information

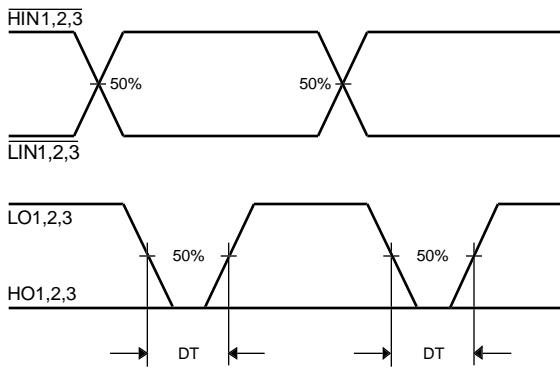
Process & Design Rule	HVDCMOS 4.0 $\mu\text{m}$	
Transistor Count	700	
Die Size	126 X 175 X 26 (mil)	
Die Outline		
Thickness of Gate Oxide		800 $\text{\AA}$
Connections	Material	Poly Silicon
First Layer	Width	4 $\mu\text{m}$
	Spacing	6 $\mu\text{m}$
	Thickness	5000 $\text{\AA}$
Second Layer	Material	Al - Si (Si: 1.0% $\pm 0.1\%$ )
	Width	6 $\mu\text{m}$
	Spacing	9 $\mu\text{m}$
	Thickness	20,000 $\text{\AA}$
Contact Hole Dimension		8 $\mu\text{m}$ X 8 $\mu\text{m}$
Insulation Layer	Material	PSG ( $\text{SiO}_2$ )
	Thickness	1.5 $\mu\text{m}$
Passivation (1)	Material	PSG ( $\text{SiO}_2$ )
	Thickness	1.5 $\mu\text{m}$
Passivation (2)	Material	Proprietary*
	Thickness	Proprietary*
Method of Saw		Full Cut
Method of Die Bond		Ablebond 84 - 1
Wire Bond	Method	Thermo Sonic
	Material	Au (1.0 mil / 1.3 mil)
Leadframe	Material	Cu
	Die Area	Ag
	Lead Plating	Pb : Sn (37 : 63)
Package	Types	28 Lead PDIP & SOIC / 44 Lead PLCC
	Materials	EME6300 / MP150 / MP190
Remarks:	* Patent Pending	



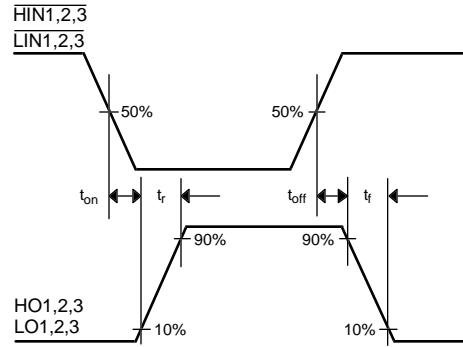
**Figure 1. Input/Output Timing Diagram**



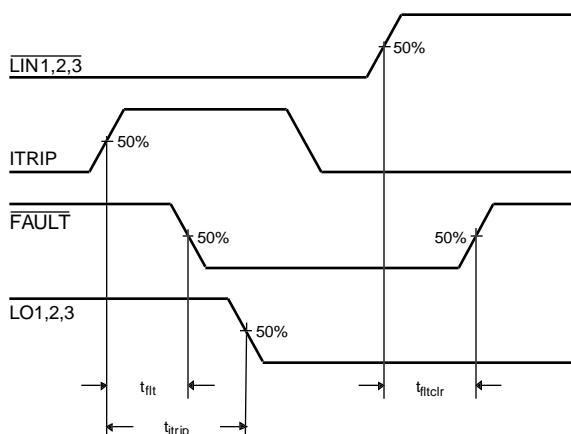
**Figure 2. Floating Supply Voltage Transient Test Circuit**



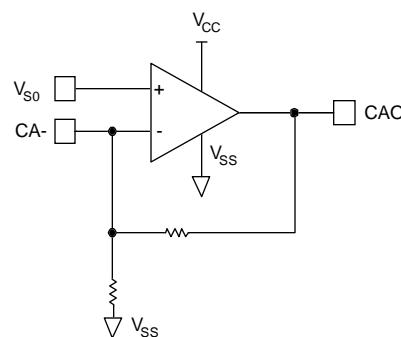
**Figure 3. Deadtime Waveform Definitions**



**Figure 4. Input/Output Switching Time Waveform Definitions**



**Figure 5. Overcurrent Shutdown Switching Time Waveform Definitions**



**Figure 6. Diagnostic Feedback Operational Amplifier Circuit**

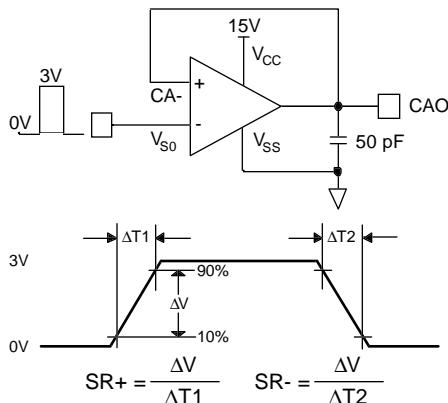


Figure 7. Operational Amplifier Slew Rate Measurement

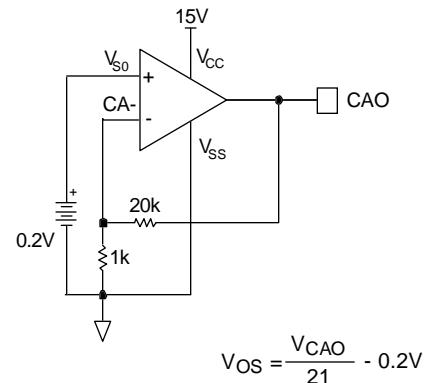
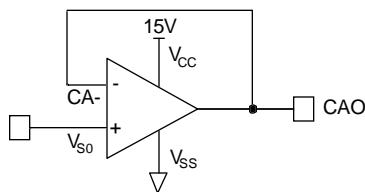


Figure 8. Operational Amplifier Input Offset Voltage Measurement



Measure  $V_{CAO1}$  at  $V_{SO} = 0.1V$   
 $V_{CAO2}$  at  $V_{SO} = 5V$

$$CMRR = -20 \cdot \log \left| \frac{(V_{CAO1}-0.1V) - (V_{CAO2}-5V)}{4.9V} \right| \text{ (dB)}$$

Figure 9. Operational Amplifier Common Mode Rejection Ratio Measurements

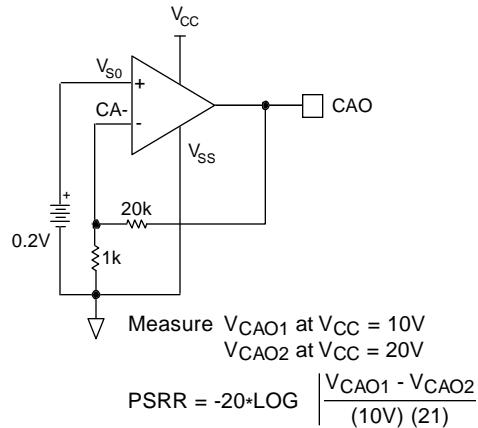


Figure 10. Operational Amplifier Power Supply Rejection Ratio Measurements

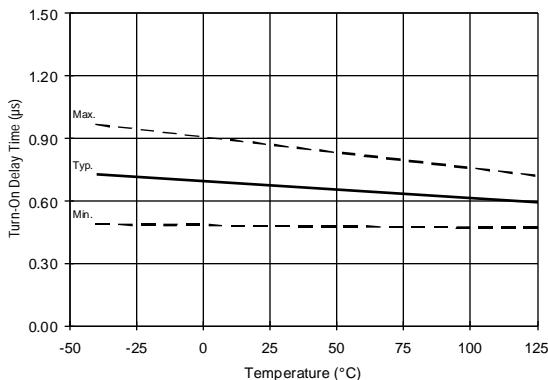


Figure 11A. Turn-On Time vs. Temperature

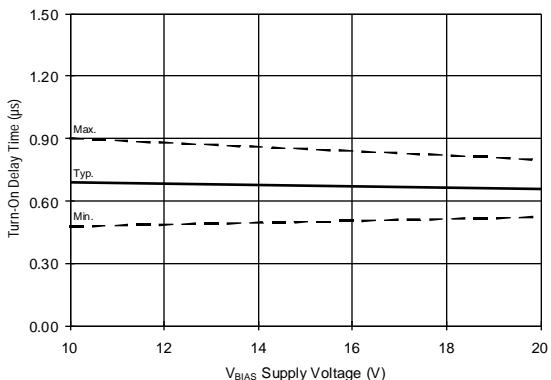


Figure 11B. Turn-On Time vs. Voltage

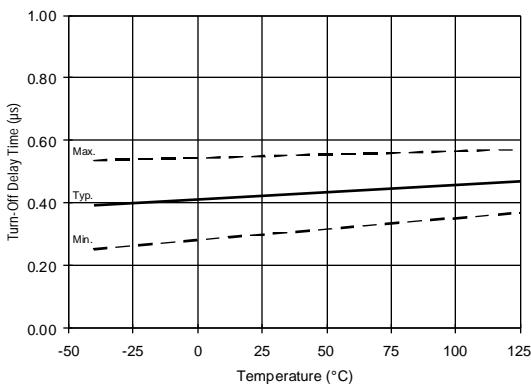


Figure 12A. Turn-Off Time vs. Temperature

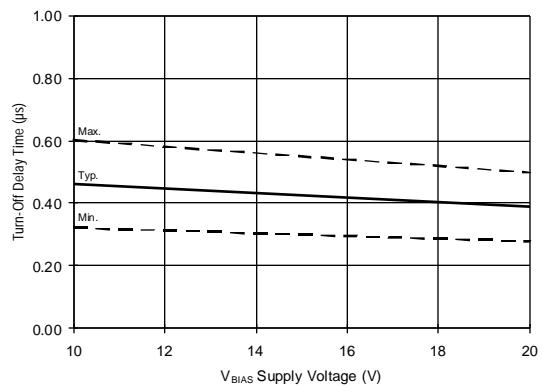


Figure 12B. Turn-Off Time vs. Voltage

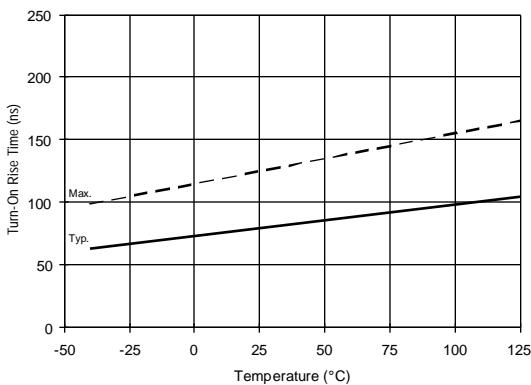


Figure 13A. Turn-On Rise Time vs. Temperature

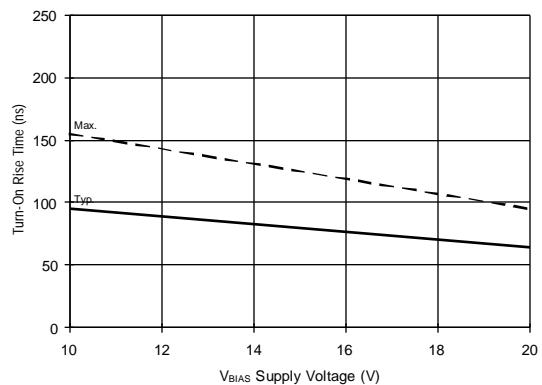


Figure 13B. Turn-On Rise Time vs. Voltage

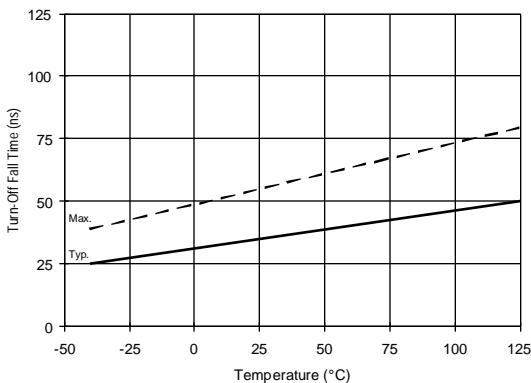


Figure 14A. Turn-Off Fall Time vs. Temperature

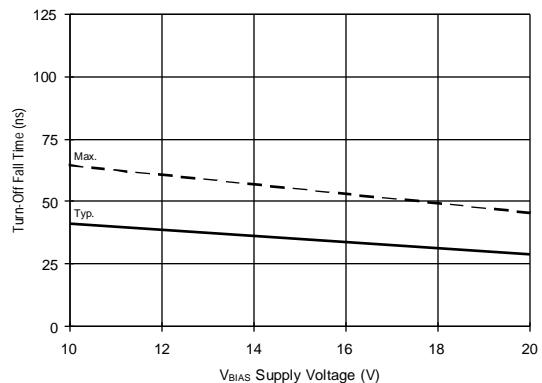
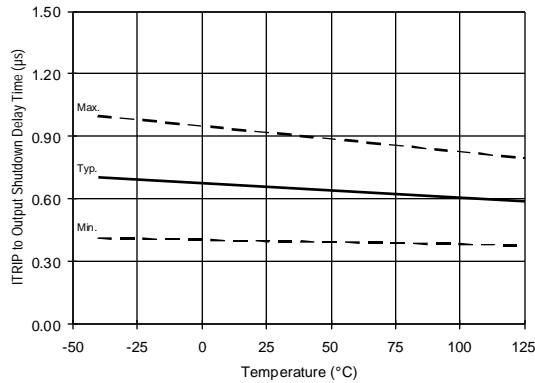
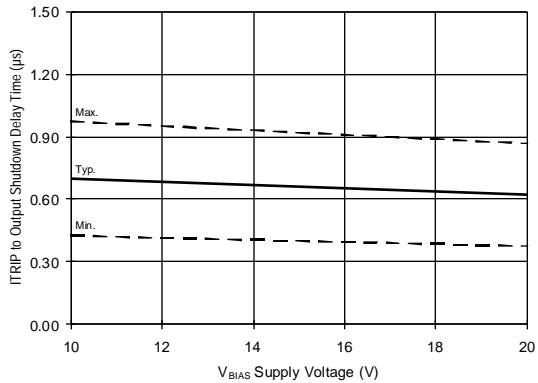


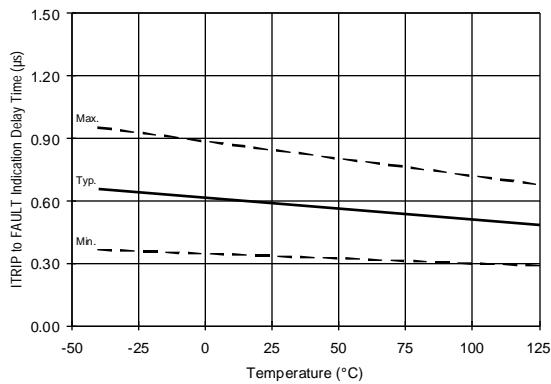
Figure 14B. Turn-Off Fall Time vs. Voltage



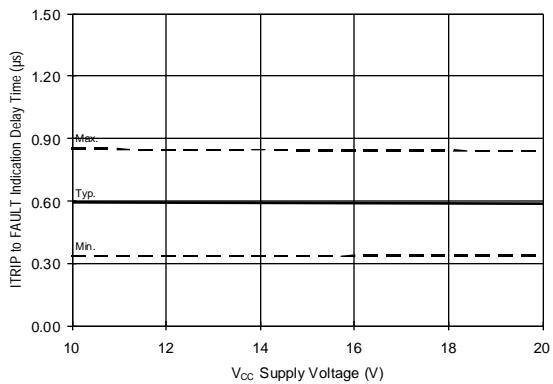
**Figure 15A. ITRIP to Output Shutdown Time vs. Temperature**



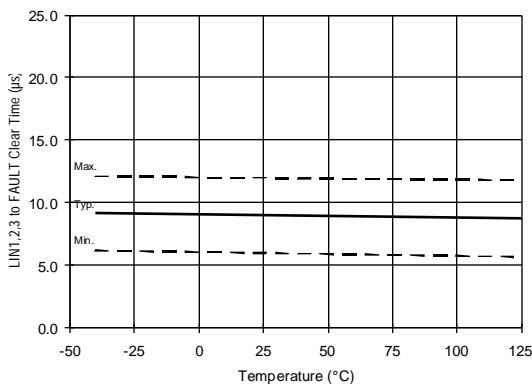
**Figure 15B. ITRIP to Output Shutdown Time vs. Voltage**



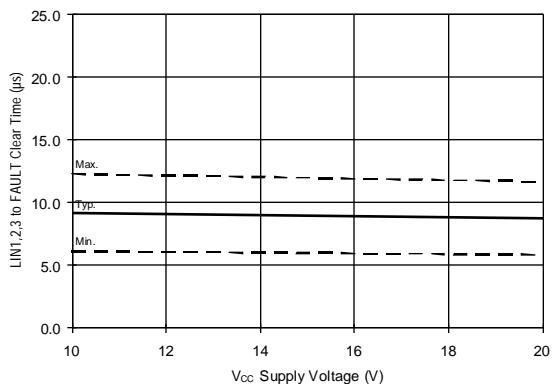
**Figure 16A. ITRIP to FAULT Indication Time vs. Temperature**



**Figure 16B. ITRIP to FAULT Indication Time vs. Voltage**



**Figure 17A. LIN1,2,3 to FAULT Clear Time vs. Temperature**



**Figure 17B. LIN1,2,3 to FAULT Clear Time vs. Voltage**

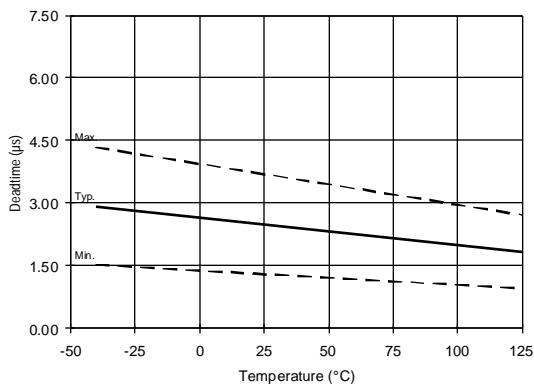


Figure 18A. Deadtime vs. Temperature

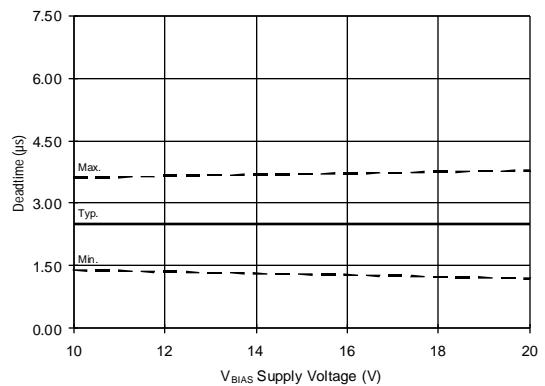


Figure 18B. Deadtime vs. Voltage

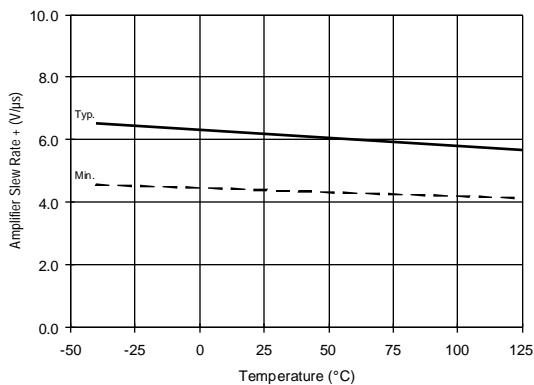


Figure 19A. Amplifier Slew Rate (+) vs. Temperature

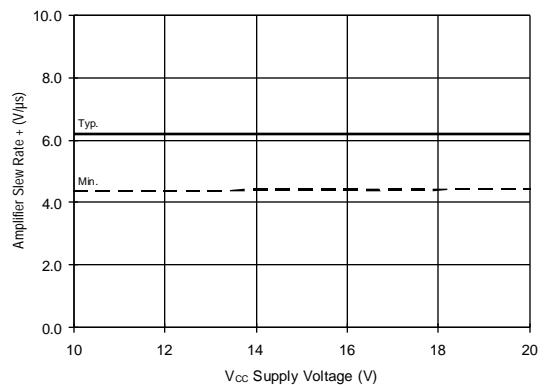


Figure 19B. Amplifier Slew Rate (+) vs. Voltage

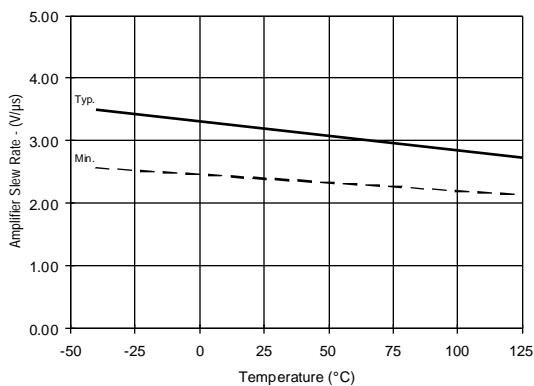


Figure 20A. Amplifier Slew Rate (-) vs. Temperature

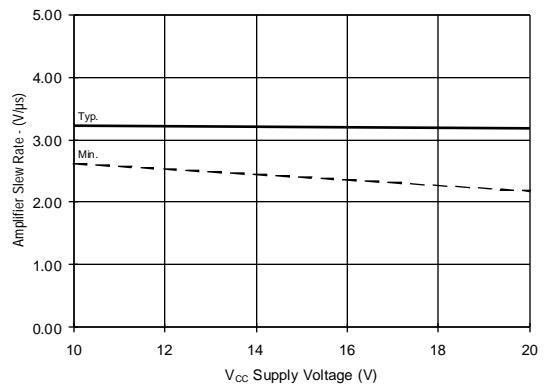


Figure 20B. Amplifier Slew Rate (-) vs. Voltage

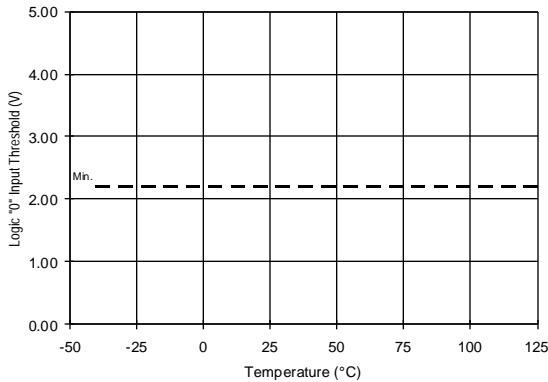


Figure 21A. Logic "0" Input Threshold vs. Temperature

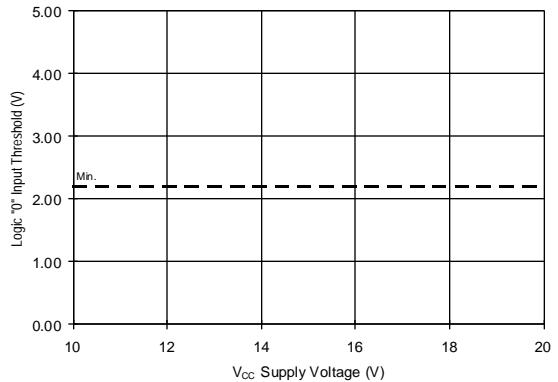


Figure 20B. Logic "0" Input Threshold vs. Voltage

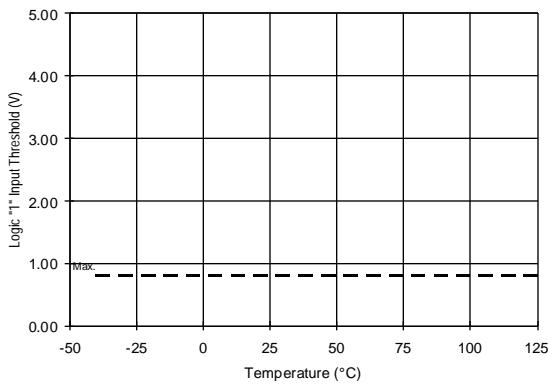


Figure 22A. Logic "1" Input Threshold vs. Temperature

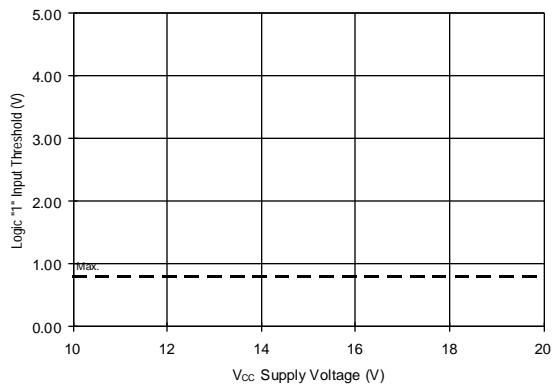


Figure 22B. Logic "1" Input Threshold vs. Voltage

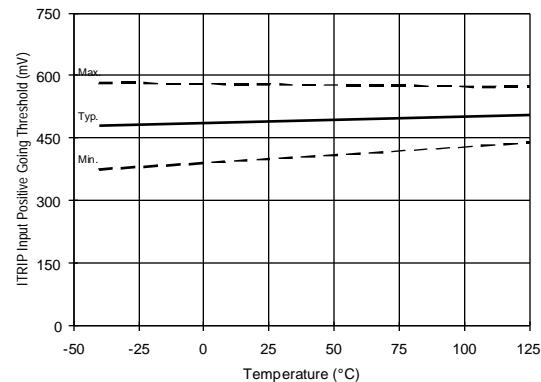


Figure 23A. ITRIP Input Positive Going Threshold vs. Temperature

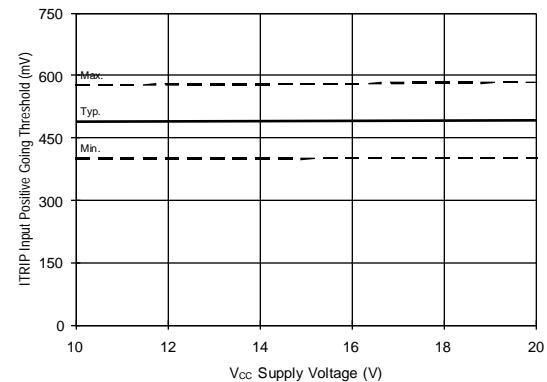
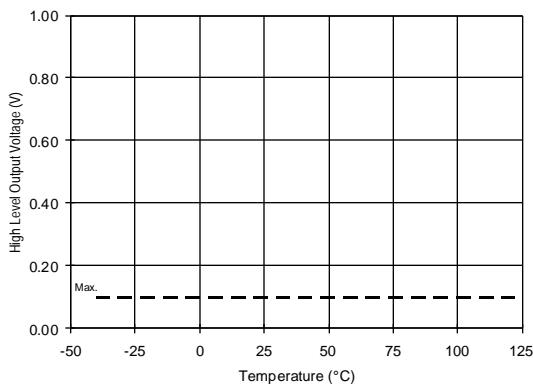
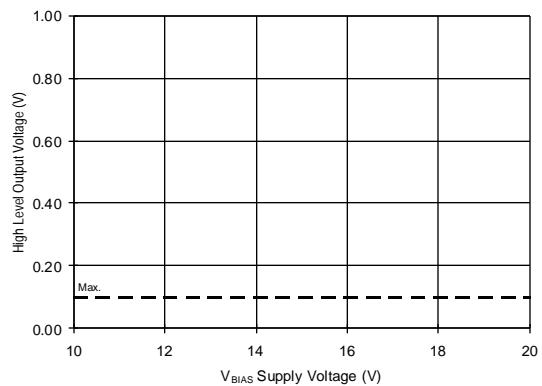


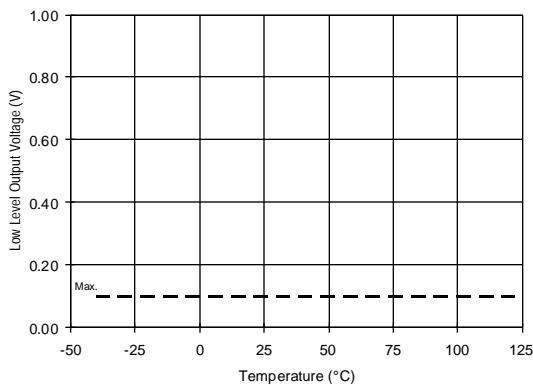
Figure 23B. ITRIP Input Positive Going Threshold vs. Voltage



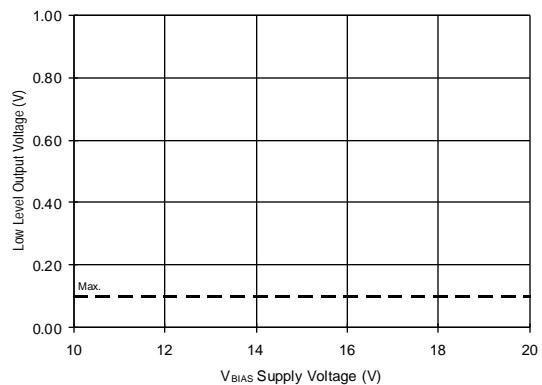
**Figure 24A. High Level Output vs. Temperature**



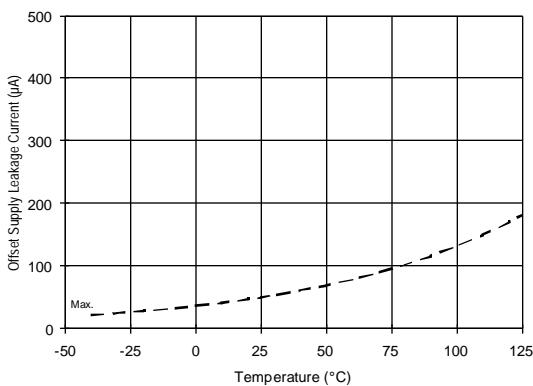
**Figure 24B. High Level Output vs. Voltage**



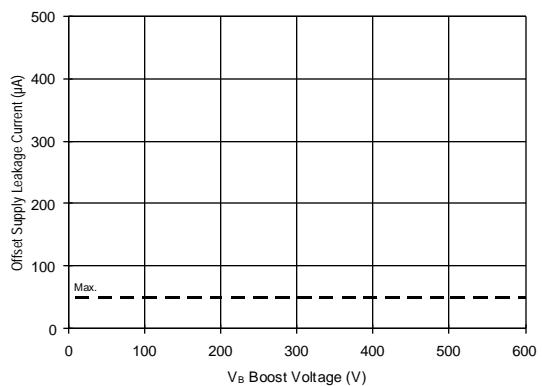
**Figure 25A. Low Level Output vs. Temperature**



**Figure 25B. Low Level Output vs. Voltage**



**Figure 26A. Offset Supply Leakage Current vs. Temperature**



**Figure 26B. Offset Supply Leakage Current vs. Voltage**

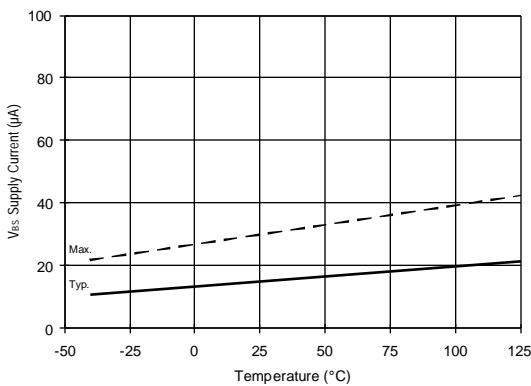


Figure 27A. V<sub>BS</sub> Supply Current vs. Temperature

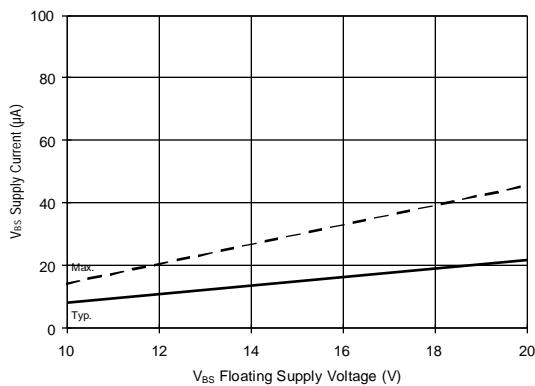


Figure 27B. V<sub>BS</sub> Supply Current vs. Voltage

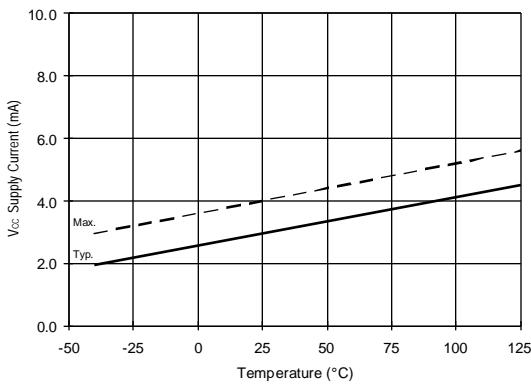


Figure 28A. V<sub>CC</sub> Supply Current vs. Temperature

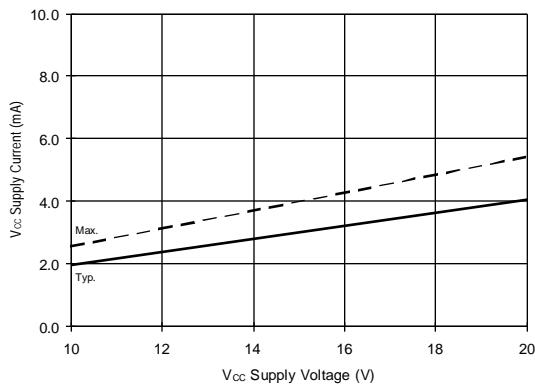


Figure 28B. V<sub>CC</sub> Supply Current vs. Voltage

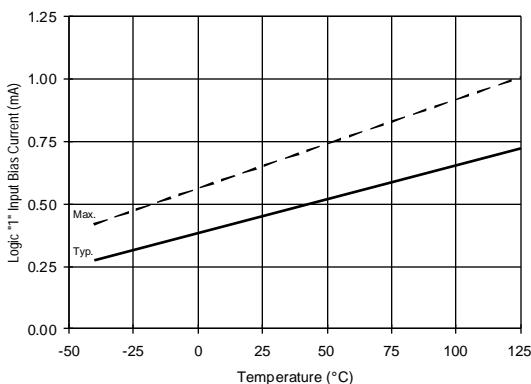


Figure 29A. Logic "1" Input Current vs. Temperature

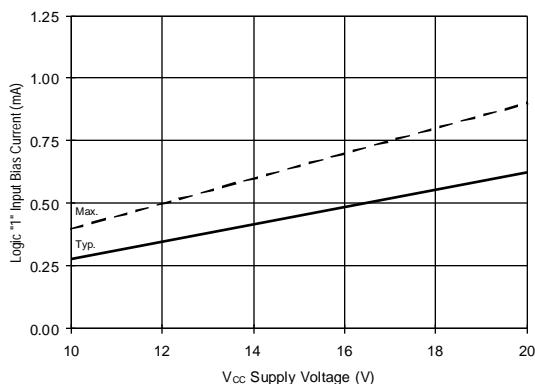


Figure 29A. Logic "1" Input Current vs. Voltage

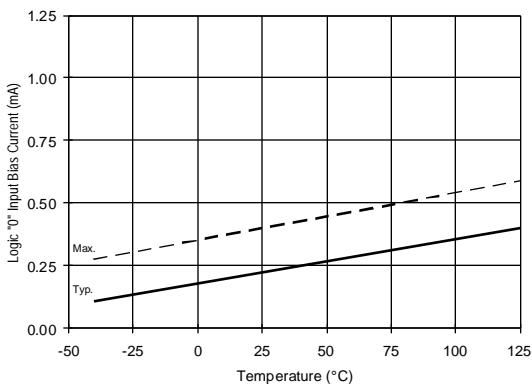


Figure 30A. Logic "0" Input Current vs. Temperature

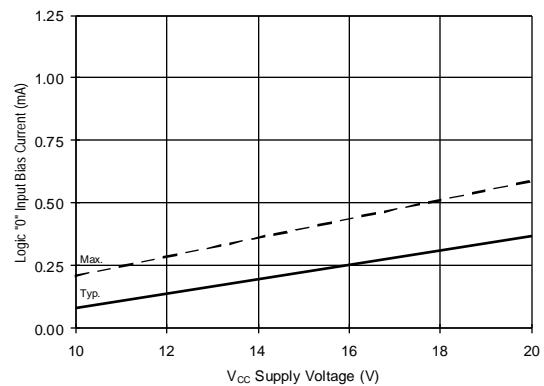


Figure 30B. Logic "0" Input Current vs. Voltage

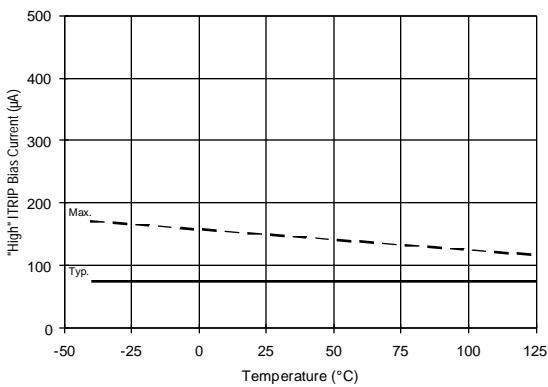


Figure 31A. "High" ITRIP Current vs. Temperature

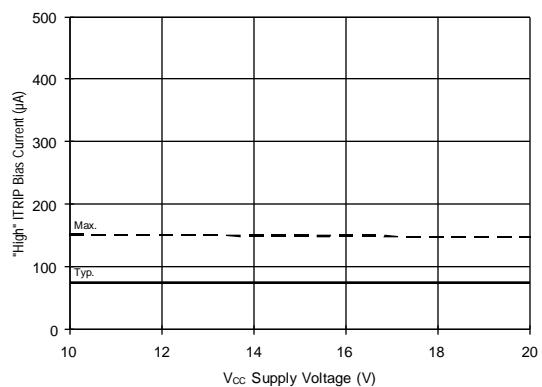


Figure 31B. "High" ITRIP Current vs. Voltage

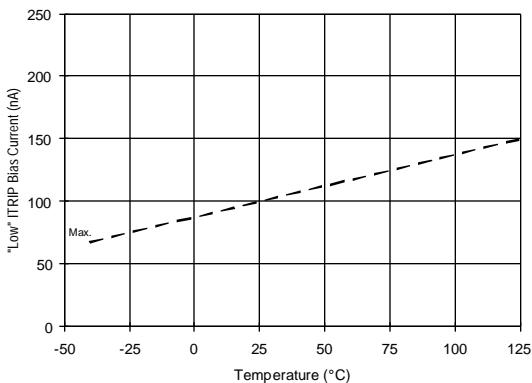


Figure 32A. "Low" ITRIP Current vs. Temperature

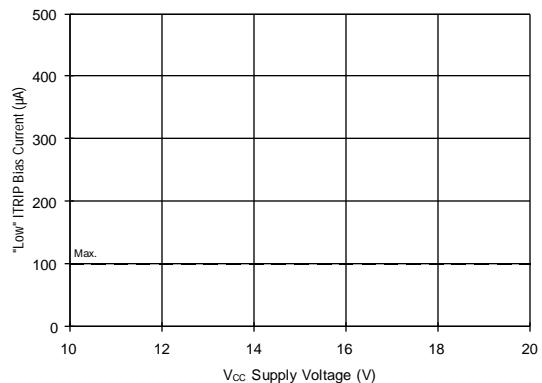


Figure 32B. "Low" ITRIP Current vs. Voltage

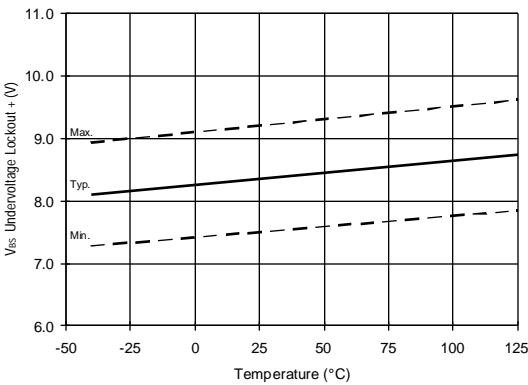


Figure 33. V<sub>BS</sub> Undervoltage (+) vs. Temperature

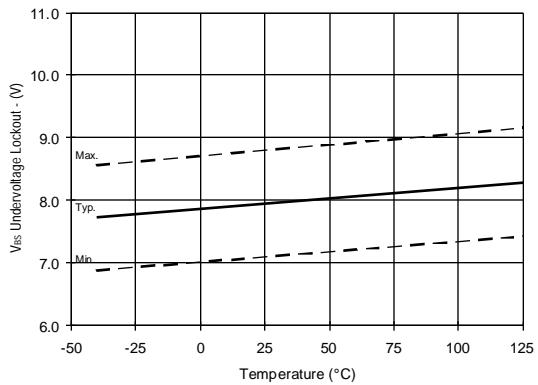


Figure 34. V<sub>BS</sub> Undervoltage (-) vs. Temperature

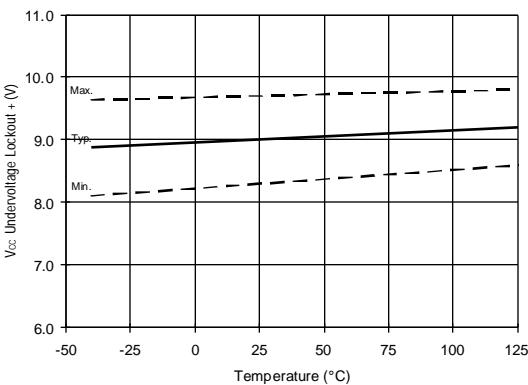


Figure 35. V<sub>CC</sub> Undervoltage (+) vs. Temperature

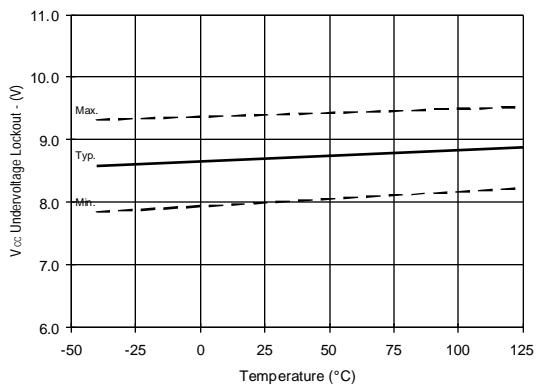


Figure 36. V<sub>CC</sub> Undervoltage (-) vs. Temperature

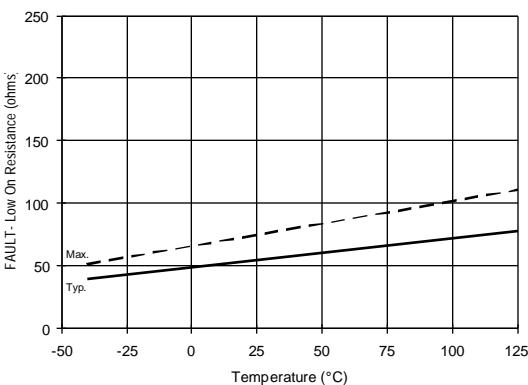


Figure 37A. FAULT Low On Resistance vs. Temperature

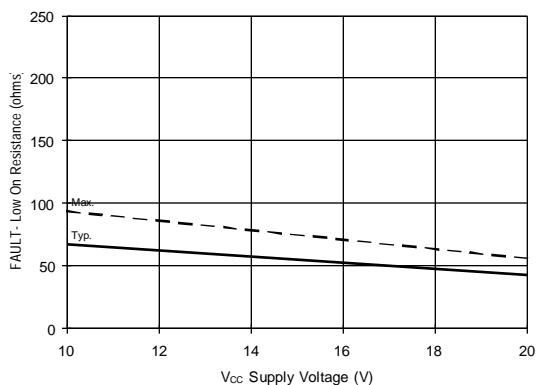
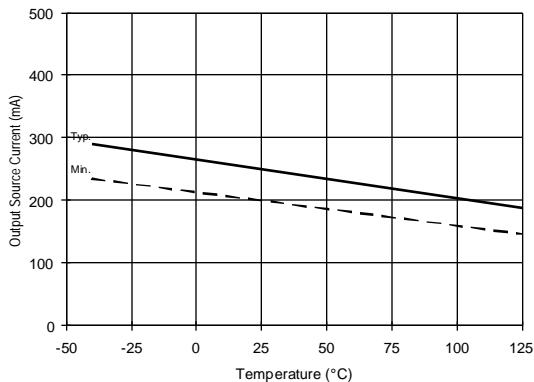
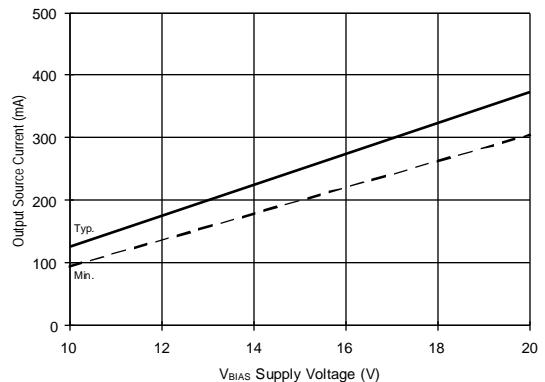


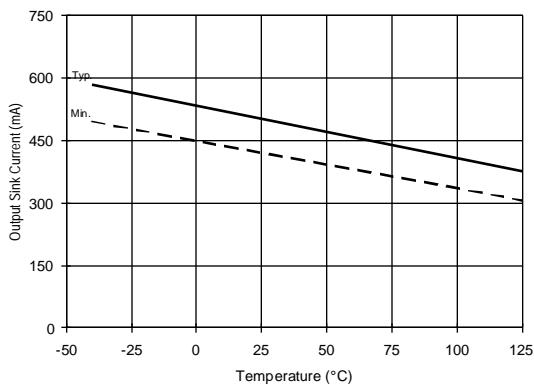
Figure 37B. FAULT Low On Resistance vs. Voltage



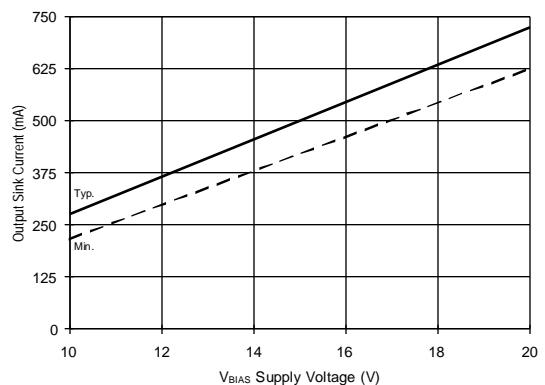
**Figure 38A. Output Source Current vs. Temperature**



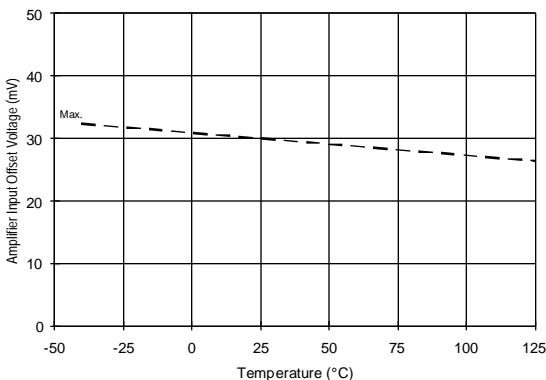
**Figure 38B. Output Source Current vs. Voltage**



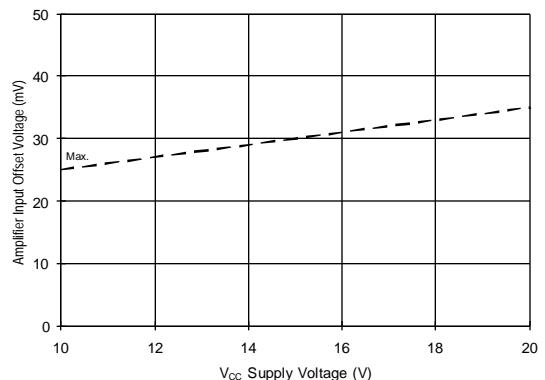
**Figure 39A. Output Sink Current vs. Temperature**



**Figure 39B. Output Sink Current vs. Voltage**



**Figure 40A. Amplifier Input Offset vs. Temperature**



**Figure 40B. Amplifier Input Offset vs. Voltage**

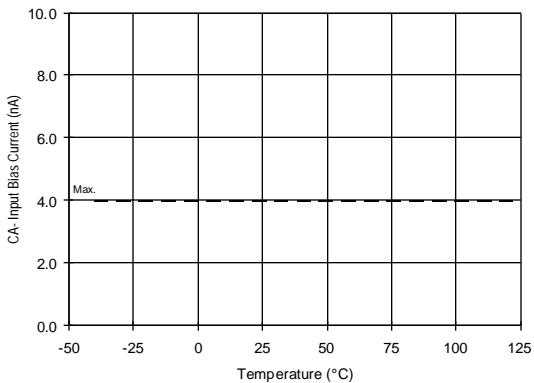


Figure 41A. CA- Input Current vs. Temperature

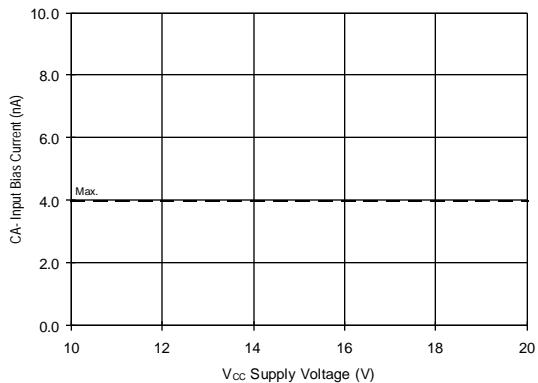


Figure 41B. CA- Input Current vs. Voltage

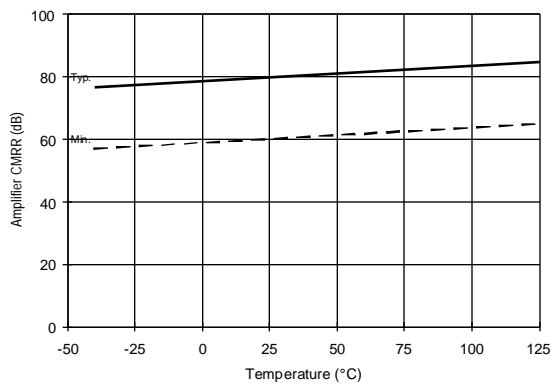


Figure 42A. Amplifier CMRR vs. Temperature

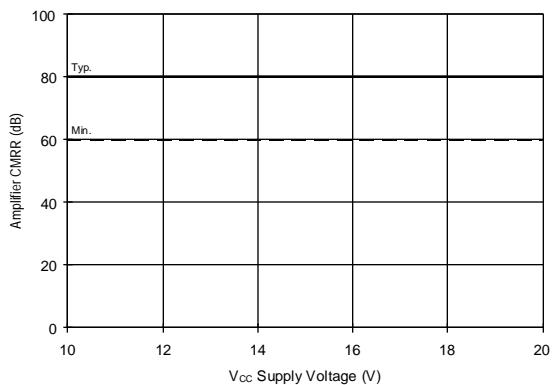


Figure 42B. Amplifier CMRR vs. Voltage

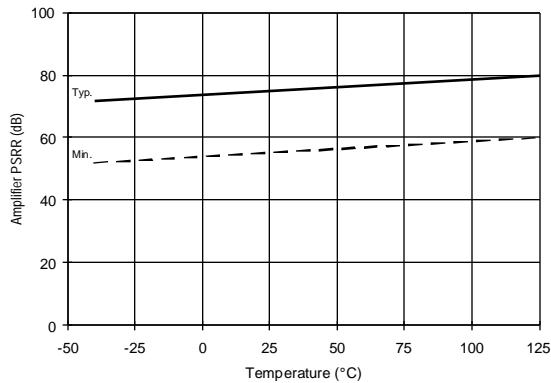


Figure 43A. Amplifier PSRR vs. Temperature

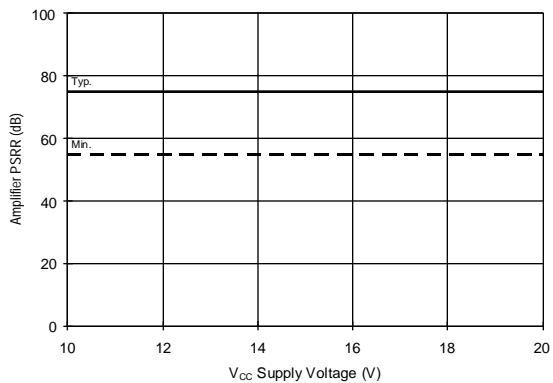
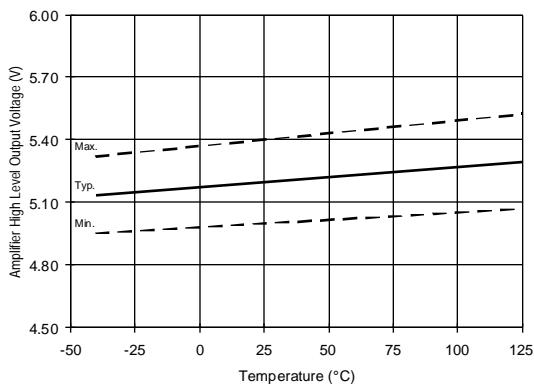
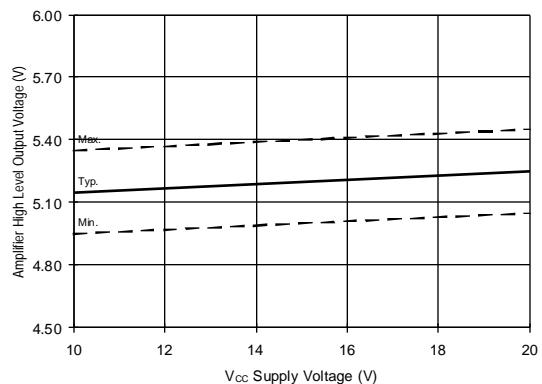


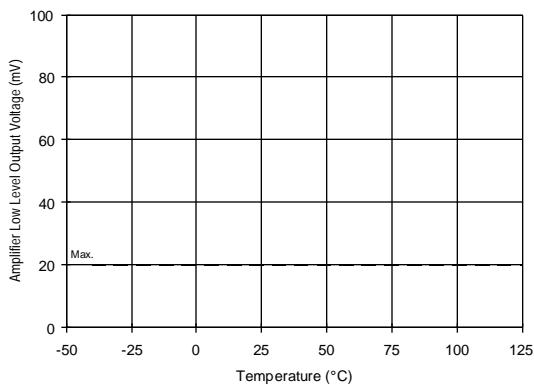
Figure 43B. Amplifier PSRR vs. Voltage



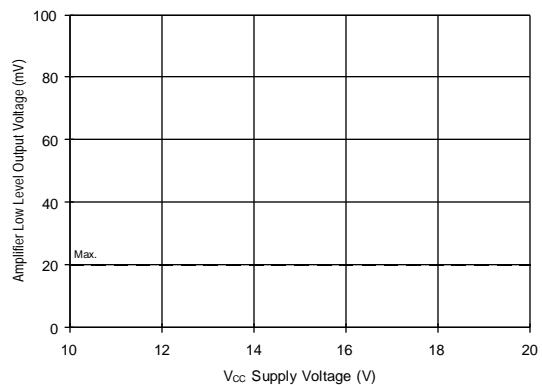
**Figure 44A. Amplifier High Level Output vs. Temperature**



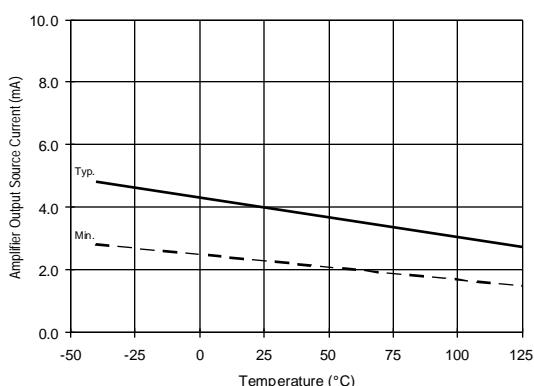
**Figure 44B. Amplifier High Level Output vs. Voltage**



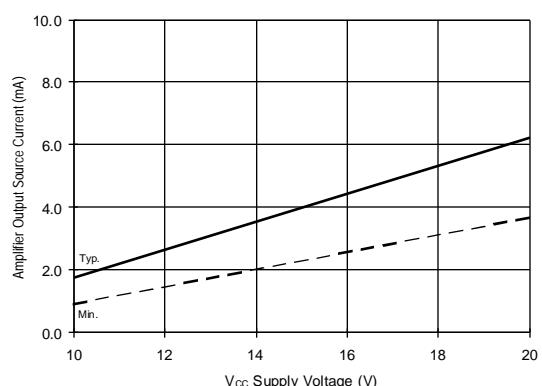
**Figure 45A. Amplifier Low Level Output vs. Temperature**



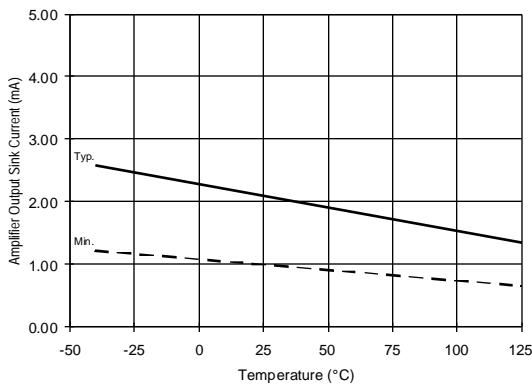
**Figure 45B. Amplifier Low Level Output vs. Voltage**



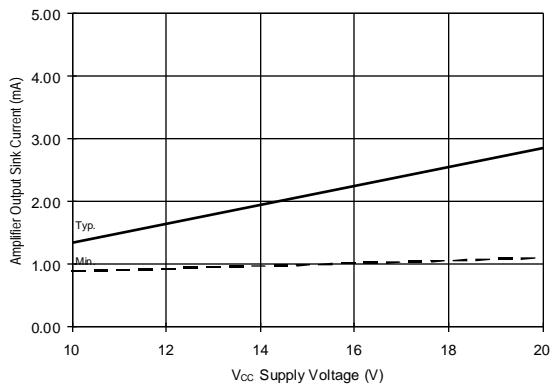
**Figure 46A. Amplifier Output Source Current vs. Temperature**



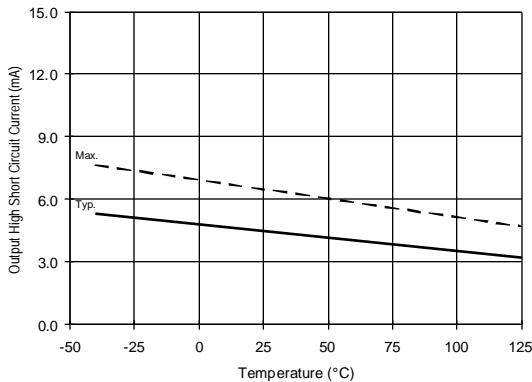
**Figure 46B. Amplifier Output Source Current vs. Voltage**



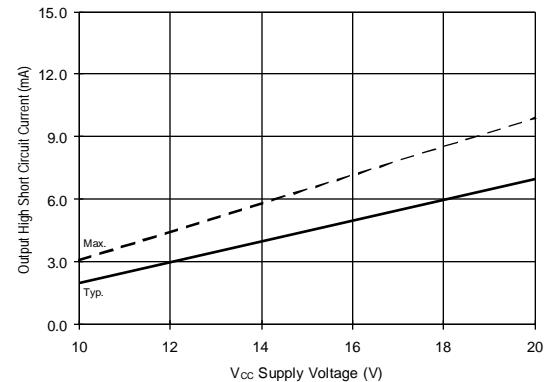
**Figure 47A. Amplifier Output Sink Current vs. Temperature**



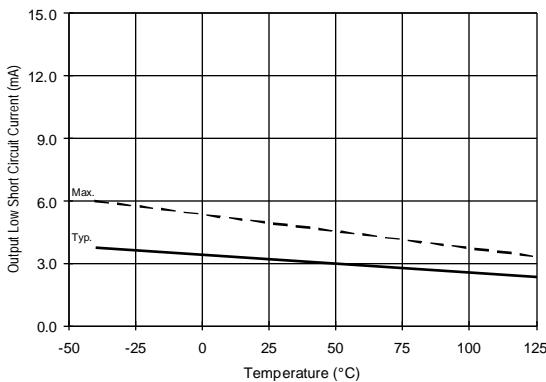
**Figure 47B. Amplifier Output Sink Current vs. Voltage**



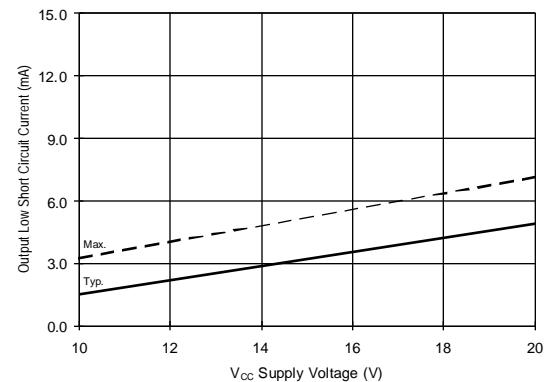
**Figure 48A. Amplifier Output High Short Circuit Current vs. Temperature**



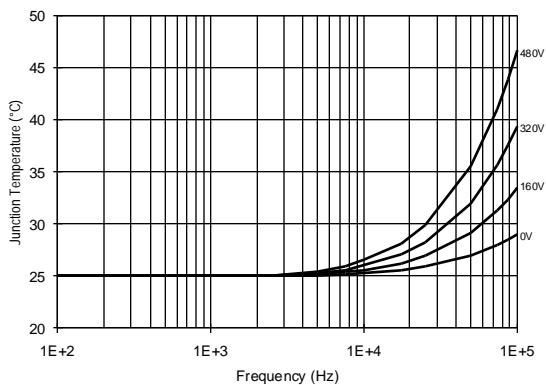
**Figure 48B. Amplifier Output High Short Circuit Current vs. Voltage**



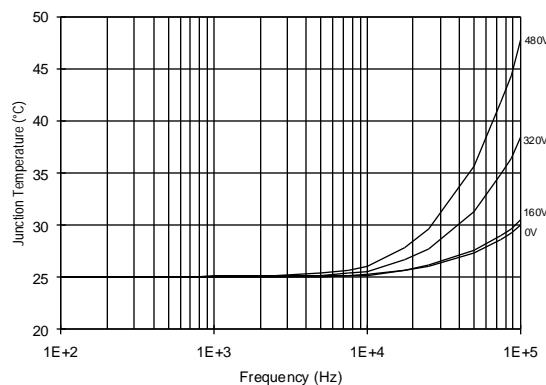
**Figure 49A. Amplifier Output Low Short Circuit Current vs. Temperature**



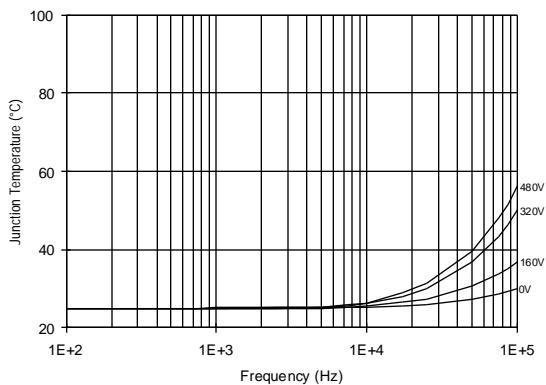
**Figure 49B. Amplifier Output Low Short Circuit Current vs. Voltage**



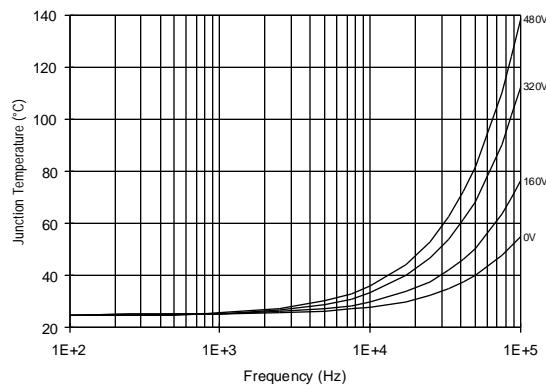
**Figure 50. IR2130  $T_J$  vs. Frequency (IRF820)**  
 $R_{GATE} = 33\Omega, V_{CC} = 15V$



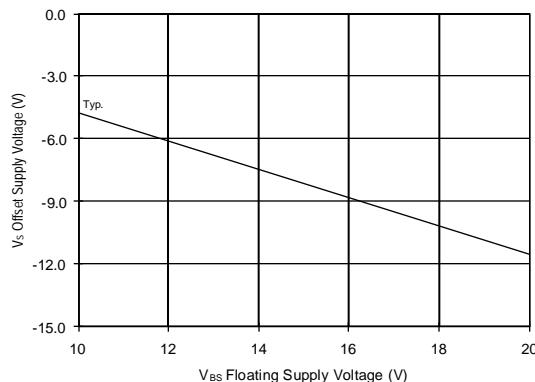
**Figure 51. IR2130  $T_J$  vs. Frequency (IRF830)**  
 $R_{GATE} = 20\Omega, V_{CC} = 15V$



**Figure 52. IR2130  $T_J$  vs. Frequency (IRF840)**  
 $R_{GATE} = 15\Omega, V_{CC} = 15V$



**Figure 53. IR2130  $T_J$  vs. Frequency (IRF450)**  
 $R_{GATE} = 10\Omega, V_{CC} = 15V$



**Figure 54. Maximum VS Negative Offset vs. V<sub>BS</sub> Supply Voltage**